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Vishay Siliconix

# N-Channel 30 V (D-S) MOSFET



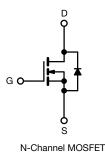
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	30				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS}$ = 10 V	0.047				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.065				
Q <sub>g</sub> typ. (nC)	3.0				
I <sub>D</sub> (A)	4.0				
Configuration	Single				

#### **FEATURES**

- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> and UIS tested







ORDERING INFORMATION				
Package	SOT-23 (TO-236)			
Lead (Pb)-free	Si2306BDS-T1-E3			
Lead (Pb)-free and halogen-free	Si2306BDS-T1-GE3			

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	30	v
Gate-source voltage		V <sub>GS</sub>	± 20	
Continuous drain current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>	T <sub>A</sub> = 25 °C		4.0 °	
	T <sub>A</sub> = 70 °C		3.5 °	
	T <sub>A</sub> = 25 °C	I <sub>D</sub>	3.16 <sup>d</sup>	
	T <sub>A</sub> = 70 °C		2.7 <sup>d</sup>	А
Pulsed drain current		I <sub>DM</sub>	20	
Continuous source-drain diode current <sup>a, b</sup>			1.04 <sup>c</sup>	
		I <sub>S</sub>	0.62 d	
Maximum power dissipation <sup>a, b</sup>	T <sub>A</sub> = 25 °C		1.25 <sup>c</sup>	
	T <sub>A</sub> = 70 °C	<u> </u>	0.8 c	W
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	0.75 <sup>d</sup>	
	T <sub>A</sub> = 70 °C		0.48 <sup>d</sup>	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- a. Surface mounted on 1" x 1" FR4 board,  $t \le 5 \text{ s}$
- b. Pulse width limited by maximum junction temperature
- c. t = 5 s
- d. Steady state

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THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT	
Maximum junction-to-ambient <sup>a</sup>	t ≤ 5 s	$R_{thJA}$	60	100		
	Steady state		130	166	°C/W	
Maximum junction-to-foot (drain)	Steady state	R <sub>thJF</sub>	60	75		

#### Note

a. Surface mounted on 1" x 1" FR4 board

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static				•	<u>'</u>		
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30	-	-	V	
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0	-	3.0	V	
Gate-body leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero allo allo adolo a mod		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	0.5	μA	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C	-	-	10		
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 4.5 \text{ V}, V_{GS} = 10 \text{ V}$	6	-	-	Α	
Drain accurac on atota vaciatance 3	Б	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 3.5 A	0 V, I <sub>D</sub> = 3.5 A - 0.038		0.047	-	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$	-	0.052	0.065	Ω	
Forward transconductance a	9 <sub>fs</sub>	$V_{DS} = 4.5 \text{ V}, I_D = 2.5 \text{ A}$	-	7.0	-	S	
Diode forward voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 1.25 A	-	0.8	1.2	V	
Dynamic							
Gate charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 2.5 \text{ A}$	-	3.0	4.5		
Total gate charge	Q <sub>gt</sub>		-	6	9	nC	
Gate-source charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2.5 \text{ A}$	-	1.6	-		
Gate-drain charge	Q <sub>gd</sub>		-	0.6	-		
Gate resistance	$R_g$	f = 1 MHz	2.0	5.0	7.5	Ω	
Input capacitance	C <sub>iss</sub>		-	305	-		
Output capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	65	-	pF	
Reverse transfer capacitance	C <sub>rss</sub>		-	29	-		
Switching							
Turn-on delay time	t <sub>d(on)</sub>		-	7	11		
Rise time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, \text{ R}_L = 15 \Omega, \text{ I}_D \cong 1 \text{ A},$	-	12	18		
Turn-off delay time	t <sub>d(off)</sub>	$V_{GEN} = 0 \text{ V}, R_g = 6 \Omega$	-	14	25	ns	
Fall time	t <sub>f</sub>		-	6	10	1	
Reverse recovery time	t <sub>rr</sub>	1 4 05 4 4:/44 400 4/ -	-	14	21	1	
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = 1.25 A, di/dt = 100 A/μs	-	6	10	nC	

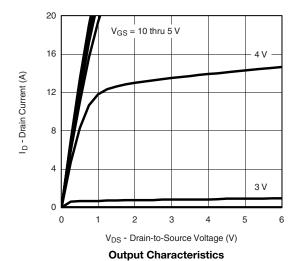
#### Notes

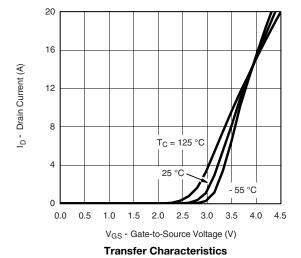
a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

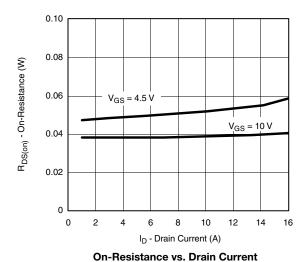
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

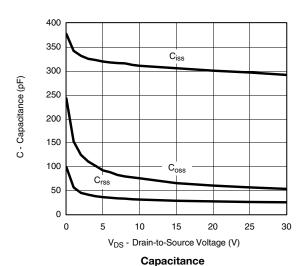


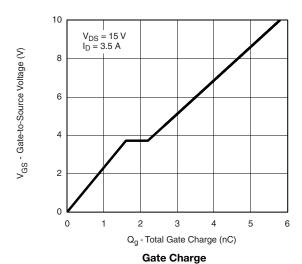
### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

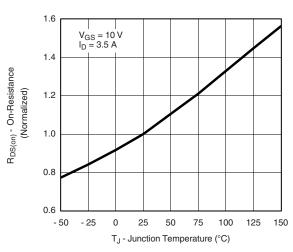






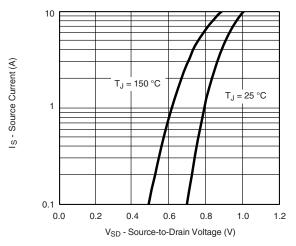




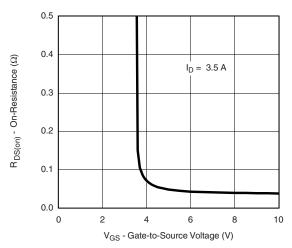




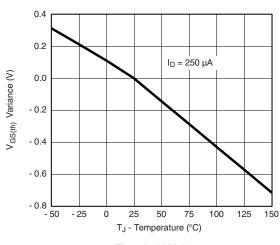
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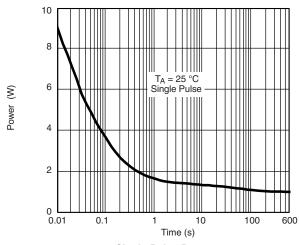
#### Source-Drain Diode Forward Voltage



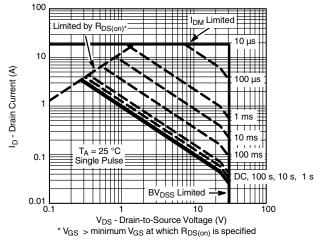
On-Resistance vs. Gate-to-Source Voltage



**Threshold Voltage** 

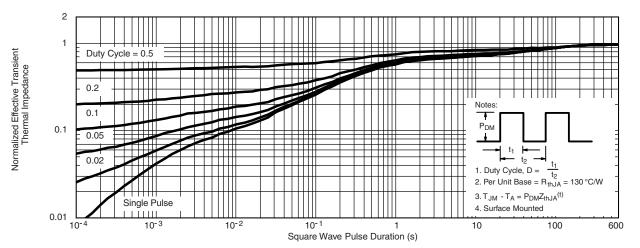


Single Pulse Power





### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

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# SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A <sub>1</sub>	0.01	0.10	0.0004	0.004	
A <sub>2</sub>	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E <sub>1</sub>	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L <sub>1</sub>	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01	•			

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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